

ABSTRACT OF THE DISCLOSURE

According to one embodiment (300), a method of forming a self-aligned contact can include forming adjacent conducting structures with sidewalls (302). A first insulating layer may then be formed without first forming a liner (304), such as a liner that is conventionally
5 formed to protect underlying conducting structures and/or a substrate. A contact hole may then be etched between adjacent conducting structures (306). Contact structures may then be formed (308).